

Vishay Siliconix

# **Precision Monolithic Quad SPST CMOS Analog Switches**

#### DESCRIPTION

The DG417B, DG418B, DG419B monolithic CMOS analog switches were designed to provide high performance switching of analog signals. Combining low power, low leakages, high speed, low on-resistance and small physical size, the DG417B series is ideally suited for portable and battery powered industrial and military applications requiring high performance and efficient use of board space. To achieve high-voltage ratings and superior switching performance, the DG417B series is built on Vishay Siliconix's high voltage silicon gate (HVSG) process. Break-before-make is guaranteed for the DG419B, which is an SPDT configuration. An epitaxial layer prevents latchup. Each switch conducts equally well in both directions when on, and blocks up to the power supply level when off. The DG417B and DG418B respond to opposite control logic levels as shown in the Truth Table.

#### BENEFITS

- Widest dynamic range
- Low signal errors and distortion
- Break-before-make switching action
- Simple interfacing
- Reduced board space
- · Improved reliability

#### FEATURES

- ± 15 V analog signal range
- On-resistance R<sub>DS(on)</sub>: 15 Ω
- Fast switching action ton: 110 ns
- TTL and CMOS compatible
- MSOP-8 and SOIC-8 package

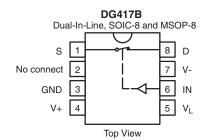
#### Note

\* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

#### APPLICATIONS

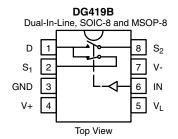
- Precision test equipment
- Precision instrumentation
- Battery powered systems
- · Sample-and-hold circuits
- Military radios
- · Guidance and control systems
- · Hard disk drivers

#### FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE							
LOGIC	DG417B	DG418B					
0	On	Off					
1	Off	On					

#### Note



TRUTH TABLE (DG419B)						
LOGIC	SW <sub>1</sub>	SW <sub>2</sub>				
0	On	Off				
1	Off	On				

Note



<sup>•</sup> Logic "0" ≤ 0.8 V

Logic "1" ≥ 2.4 V

<sup>•</sup> Logic "0" ≤ 0.8 V Logic "1" ≥ 2.4 V





ORDERING INFORMATION								
TEMP. RANGE	PACKAGE	PART NUMBER						
DG417B, DG418B								
		DG417BDY-E3 DG417BDY-T1-E3						
-40 °C to +85 °C	8-pin narrow SOIC	DG418BDY-E3 DG418BDY-T1-E3						
	8-pin MSOP	DG417BDQ-T1-E3						
		DG418BDQ-T1-E3						
DG419B								
-40 °C to +85 °C	8-pin narrow SOIC	DG419BDY-E3 DG419BDY-T1-E3						
	8-pin MSOP	DG419BDQ-T1-E3						

<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_A = 25 \text{ °C}$ , unless otherwise noted)						
PARAMETER		LIMIT	UNIT			
V-		-20				
V+		20				
GND		25	v			
VL		(GND - 0.3) to (V+) + 0.3	•			
Digital inputs <sup>a</sup> , V <sub>S</sub> , V <sub>D</sub>		(V-) - 2 to (V+) + 2 or 30 mA, whichever occurs first				
Current (any terminal) continuous	;	30				
Current (S or D) pulsed at 1 ms,	10 % duty cycle	100	— mA			
Storage temperature		-65 to +150	°C			
	8-pin narrow SOIC <sup>d</sup>	400				
Power dissipation (package) <sup>b</sup>	8-pin MSOP <sup>e</sup>	400	mW			
F	8-pin CerDIP <sup>e</sup>	600				

Notes

a. Signals on S<sub>X</sub>, D<sub>X</sub>, or IN<sub>X</sub> exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings

b. All leads welded or soldered to PC board

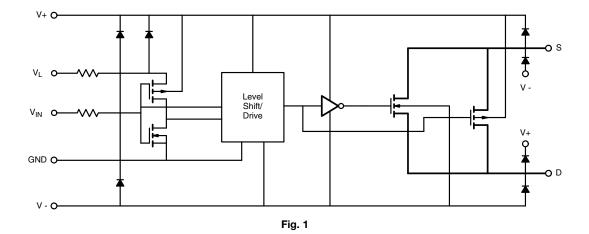
c. Derate 5.3 mW/°C above 75 °C

d. Derate 4 mW/°C above 70 °C

e. Derate 8 mW/°C above 75 °C



### SCHEMATIC DIAGRAM (Typical Channel)





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SPECIFICATIONS <sup>a</sup>										
PARAMETER	SYMBOL		ECIFIED	TEMP. <sup>b</sup>	TYP. °	<b>A SUFFIX</b> -55 °C to +125 °C		<b>D SUFFIX</b> -40 °C to +85 °C		UNIT
	01mb0E	V+ = 15 V, V- = -15 V <sub>L</sub> = 5 V, V <sub>IN</sub> = 2.4 V, 0	$V_{+} = 15 V, V_{-} = -15 V,$ $V_{-} = 5 V, V_{-} = 2.4 V, 0.8 V^{f}$			MIN. d	MAX. d	MIN. d	MAX. d	UNIT
Analog Switch										
Analog signal range <sup>e</sup>	V <sub>ANALOG</sub>			Full	-	-15	15	-15	15	V
Drain-source		I <sub>S</sub> = -10 mA, V <sub>D</sub> = ± 12	2.5 V,	Room	15	-	25	-	25	0
on-resistance	R <sub>DS(on)</sub>	V+ = 13.5 V, V- = -13		Full	-	-	34	-	29	Ω
	1			Room	-0.1	-0.25	0.25	-0.25	0.25	
	I <sub>S(off)</sub>			Full	-	-20	20	-5	5	
Switch off leakage current		$V_{+} = 16.5, V_{-} = -16.5 V$ $V_{D} = \pm 15.5 V,$	DG417B	Room	-0.1	-0.25	0.25	-0.25	0.25	
Switch off leakage current	1	$V_{\rm D} = \pm 15.5 \text{ V},$ $V_{\rm S} = \pm 15.5 \text{ V}$	DG418B	Full	-	-20	20	-5	5	
	I <sub>D(off)</sub>	, i i i i i i i i i i i i i i i i i i i	DG419B	Room	-0.1	-0.75	0.75	-0.75	0.75	nA
			DG419D	Full	-	-60	60	-12	12	
			DG417B	Room	-0.4	-0.4	0.4	-0.4	0.4	
Channel on leakage	I- C - C	V+ = 16.5 V, V- = -16.5 V	DG418B	Full	-	-40	40	-10	10	
current	I <sub>D(on)</sub>	$V_{S} = V_{D} = \pm 15.5 V$	DG419B	Room	-0.4	-0.75	0.75	-0.75	0.75	
			DG419D	Full	-	-60	60	-12	12	
Digital Control										
Input current V <sub>IN</sub> low	IIL			Full	-	-0.5	0.5	-0.5	0.5	μA
Input current V <sub>IN</sub> high	IIH			Full	-	-0.5	0.5	-0.5	0.5	μA
Dynamic Characteristics										
Turn-on time	t <sub>on</sub>	$R_L = 300 \Omega$ , $C_L = 35 pF$ , $V_S = \pm 10 V$ , see Switching	DG417B	Room	62	-	89	-	89	
rum-on lime			DG418B	Full	-	-	106	-	99	
Turn-off time	+	$v_{S} = \pm 10 v$ , see Switching Time Test Circuit	DG417B	Room	53	-	80	-	80	
rum-on lime	t <sub>off</sub>		DG418B	Full	-	-	88	-	86	ns
Transition time	+	$R_L = 300 \Omega$ , $C_L = 35 pF$ ,	DG419B	Room	60	-	87	-	87	. 115
Transmontime	t <sub>TRANS</sub>	$V_{S1} = \pm 10 \text{ V}, V_{S2} = \pm 10 \text{ V}$	DG419D	Full	-	-	96	-	93	
Break-before-make time delay	t <sub>D</sub>		DG419B	Room	16	3	-	3	-	
Charge injection	Q	$C_L = 10 \text{ nF}, V_{gen} = 0 \text{ V}, \text{ R}_g$	$gen = 0 \Omega$	Room	38	-	-	-	-	рС
Off isolation <sup>e</sup>	OIRR	$R_L = 50 \Omega, C_L = 5 pF, f =$	1 MHz	Room	-82	-	-	-	-	
Channel-to-channel crosstalk <sup>e</sup>	X <sub>TALK</sub>		DG419B	Room	-88	-	-	-	-	dB
Source off capacitance <sup>e</sup>	C <sub>S(off)</sub>			Room	12					
Drain off capacitance <sup>e</sup>	C <sub>D(off)</sub>	f = 1 MHz, V <sub>S</sub> = 0 V	DG417B DG418B	Room	12					pF
Channel on capacitance <sup>e</sup>	C <sub>D(on)</sub>	f = 1 MHz, V <sub>S</sub> = 0 V	DG417B DG418B	Room	50					р
			DG419B	Room	57					
Power Supplies		1			1			1	1	
Positive supply current	l+			Room	0.001	-	1	-	1	
				Full	-	-	5	-	5	
Negative supply current	I-	V+ = 16.5 V, V- = -16.5 V,		Room	-0.001	-1	-	-1	-	
- Jan - Coppi, Conon	1-			Full	-	-5	-	-5	-	μA
Logic supply current	V <sub>IN</sub> = 0 V or 5 V		Room	0.001	-	1	-	1	г	
. <u>3.1</u>	·L			Full	-	-	5	-	5	
Ground current	I <sub>GND</sub>			Room	-0.001	-1	-	-1	-	4
	GIND			Full	-	-5	-	-5	-	

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SPECIFICATIONS <sup>a</sup>										
PARAMETER	SYMBOL	$\label{eq:symbol} \textbf{SYMBOL} \left  \begin{array}{c} \textbf{TEST CONDITIONS} \\ \textbf{UNLESS OTHERWISE SPECIFIED} \\ V+ = 12 \ V, \ V- = 0 \ V, \\ V_L = 5 \ V, \ V_{IN} = 2.4 \ V, \ 0.8 \ V^{f} \end{array} \right  .$		TEMP. <sup>b</sup>	TYP. °	<b>A SUFFIX</b> -55 °C to +125 °C		<b>D SUFFIX</b> -40 °C to +85 °C		UNIT
	0111202					MIN. d	MAX. d	MIN. d	MAX. d	••••
Analog Switch										
Analog signal range <sup>e</sup>	VANALOG			Full	-	0	12	0	12	V
Drain-source	R <sub>DS(on)</sub>	I <sub>S</sub> = -10 mA, V <sub>D</sub> = 3.	8 V,	Room	26	-	35	-	35	Ω
on-resistance	US(on)	V+ = 10.8 V		Full	-	-	52	-	45	32
Dynamic Characteristics	6									
Turn-on time	t <sub>on</sub>		_	Room	100	-	125	-	125	
	Son	$R_L = 300 \Omega, C_L = 35$ $V_S = 8 V, see Switching T$		Full	-	-	155	-	143	
Turn-off time	t <sub>off</sub>	Circuit		Room	38	-	66	-	66	ns
	чоп				-	-	73	-	69	
Break-before-make time delay	t <sub>D</sub>	$R_L = 300 \ \Omega$ , $C_L = 35 \ pF$	DG419B	Room	62	25	-	25	-	
Transition time	+	$R_L = 300 \ \Omega, \ C_L = 35 \ pF,$		Room	95	-	119	-	119	
Transition time	t <sub>TRANS</sub>	$V_{S1} = 0 V, 8 V, V_{S2} = 8$	V, 0 V	Full	-	-	153	-	141	
Charge injection	Q	$C_L$ = 10 nF, $V_{gen}$ = 0 V, R	$_{gen} = 0 \ \Omega$	Room	18	-	-	-	-	рС
Power Supplies										
Positive supply current	1+			Room	0.001	-	1	-	1	
r ositive supply current	IŦ			Full	-	-	5	-	5	
Negative supply current	I-			Room	-0.001	-1	-	-1	-	
Negative supply current	1		V+ = 13.2 V, V <sub>L</sub> = 5.25 V,		-	-5	-	-5	-	μA
Logic supply current	١L	$V_{IN} = 0 V \text{ or } 5 V$		Room	0.001	-	1	-	1	μΛ
	'L			Full	-	-	5	-	5	
Ground current	I <sub>GND</sub>				-0.001	-1	-	-1	-	
	GND		Full	-	-5	-	-5	-		

Notes

a. Refer to PROCESS OPTION FLOWCHART

b. Room = 25 °C, full = as determined by the operating temperature suffix

c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing

d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet

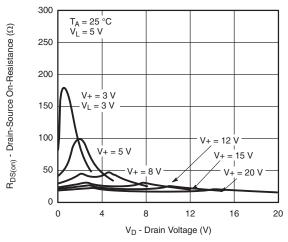
e. Guaranteed by design, not subject to production test

f.  $V_{IN}$  = input voltage to perform proper function

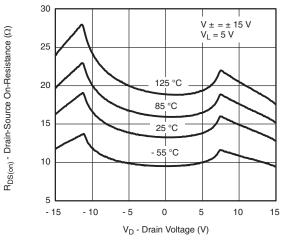
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



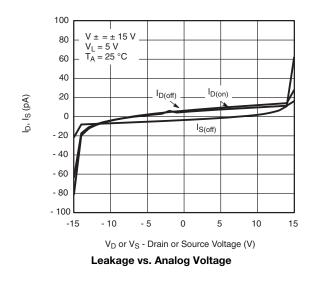
### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)

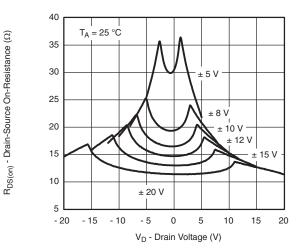


On-Resistance vs. V<sub>D</sub> and Unipolar Power

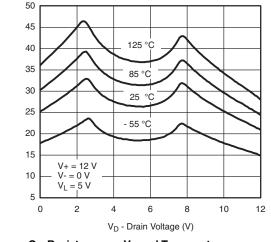


On-Resistance vs. V<sub>D</sub> and Temperature

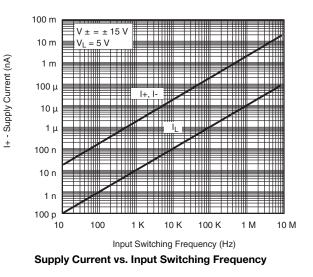




On-Resistance vs. V<sub>D</sub> and Dual Supply Voltage



On-Resistance vs. V<sub>D</sub> and Temperature



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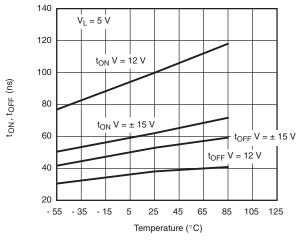
 $R_{\text{DS(on)}}$  - Drain-Source On-Resistance  $(\Omega)$ 

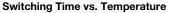
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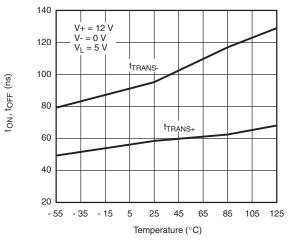


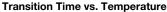
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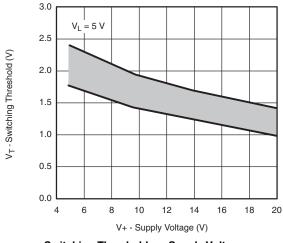
## **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



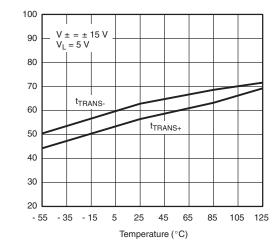






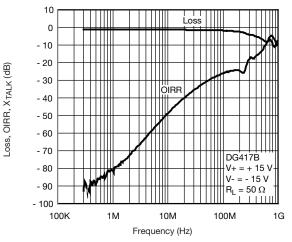


Switching Threshold vs. Supply Voltage

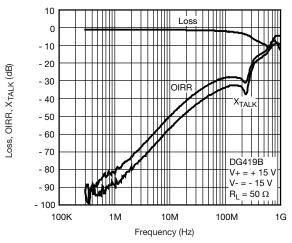


ON, tOFF (ns)

**Transition Time vs. Temperature** 



Insertion Loss, Off -Isolation Crosstalk vs. Frequency



Insertion Loss, Off -Isolation Crosstalk vs. Frequency

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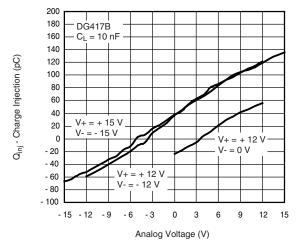
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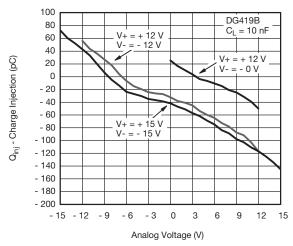


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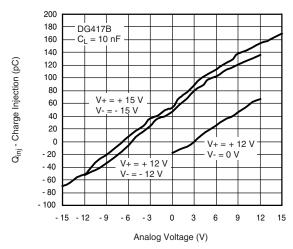
#### TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



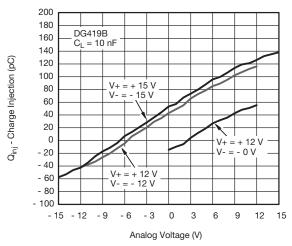
Charge Injection vs. Analog Voltage (measured at drain pin)



Charge Injection vs. Analog Voltage (measured at drain pin)



Charge Injection vs. Analog Voltage (measured at source pin)



Charge Injection vs. Analog Voltage (measured at source pin)

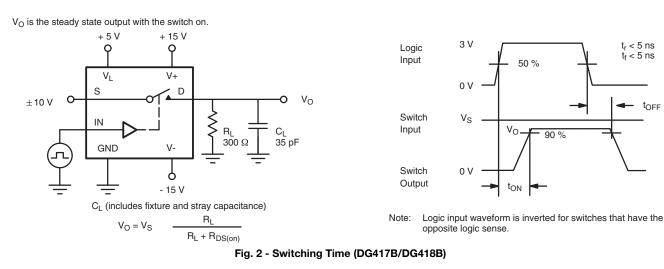


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t<sub>r</sub> < 5 ns t<sub>f</sub> < 5 ns

tOFF

#### **TEST CIRCUITS**



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t<sub>r</sub> < 5 ns t<sub>f</sub> < 5 ns

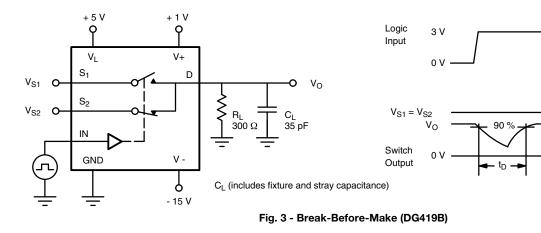
tΓ

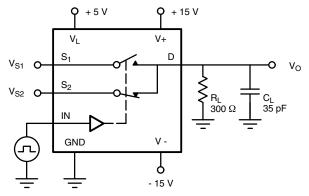
DG417B, DG418B, DG419B

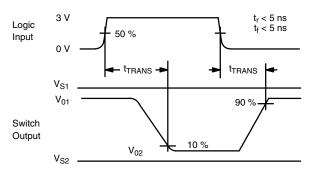
#### **TEST CIRCUITS**

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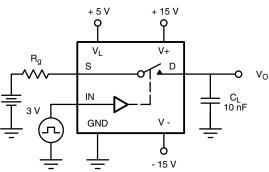


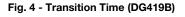




C<sub>L</sub> (includes fixture and stray capacitance)

 $V_{O} = V_{S} \qquad \frac{R_{L}}{R_{L} + r_{DS(on)}}$ 





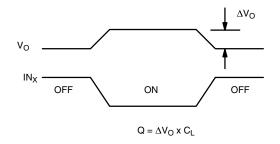
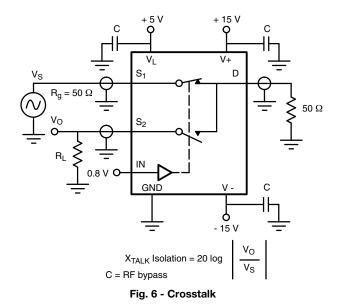


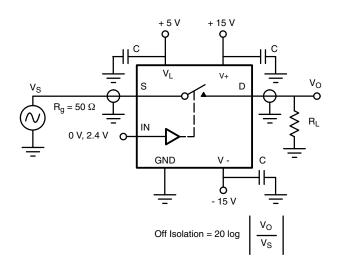
Fig. 5 - Charge Injection





#### **TEST CIRCUITS**







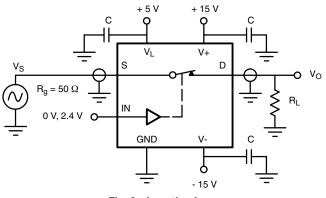


Fig. 8 - Insertion Loss

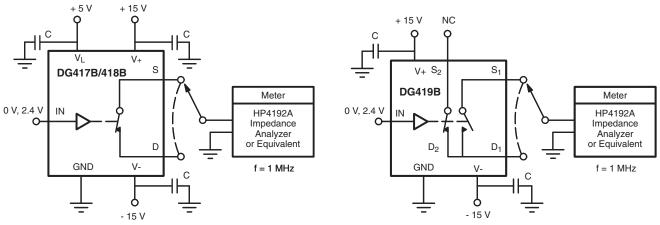


Fig. 9 - Source/Drain Capacitances

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PRODUCT SUN	IMARY					
Part number	DG417B	DG417B	DG418B	DG418B	DG419B	DG419B
Status code	2	2	2	2	2	2
Configuration	SPST x 1, NC	SPST x 1, NC	SPST x 1, NO	SPST x 1, NO	SPDT x 1	SPDT x 1
Single supply min. (V)	5	5	5	5	5	5
Single supply max. (V)	36	36	36	36	36	36
Dual supply min. (V)	5	5	5	5	5	5
Dual supply max. (V)	20	20	20	20	20	20
On-resistance ( $\Omega$ )	15	15	15	15	15	15
Charge injection (pC)	38	38	38	38	38	38
Source on capacitance (pF)	50	50	50	50	57	57
Source off capacitance (pF)	12	12	12	12	12	12
Leakage switch on typ. (nA)	0.4	0.4	0.4	0.4	0.4	0.4
Leakage switch off max. (nA)	0.25	0.25	0.25	0.25	0.75	0.75
-3 dB bandwidth (MHz)	-	-	-	-	-	-
Package	SO-8 (narrow) AS	MSOP-8	SO-8 (narrow) AS	MSOP-8	SO-8 (narrow) AS	MSOP-8
Functional circuit / applications	Multi purpose, instrumentation, medical and healthcare					
Interface	Parallel	Parallel	Parallel	Parallel	Parallel	Parallel
Single supply operation	Yes	Yes	Yes	Yes	Yes	Yes
Dual supply operation	Yes	Yes	Yes	Yes	Yes	Yes
Turn on time max. (ns)	89	89	89	89	89	89
Crosstalk and off isolation	-88	-88	-88	-88	-88	-88

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